

2SK3512-01L,S,SJ

FUJI POWER MOSFET

Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic

Absolute maximum ratings (T_c=25°C unless otherwise specified)

Items	Symbol	Ratings	Units
Drain-source voltage	V _{DS}	500	V
Continuous drain current	I _D	±14	A
Pulsed drain current	I _{D (puls)}	±56	A
Gate-source voltage	V _{GS}	±30	V
Repetitive or non-repetitive	I _{AR} (*2)	14	A
Maximum Avalanche Energy	E _{AS} (*1)	188.2	mJ
Maximum Drain-Source dV/dt	dV _{DS} /dt (*4)	20	kV/μs
Peak Diode Recovery dV/dt	dV/dt (*3)	5	kV/μs
Max. power dissipation	P _D	T _a =25°C	1.67
		T _c =25°C	195
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C

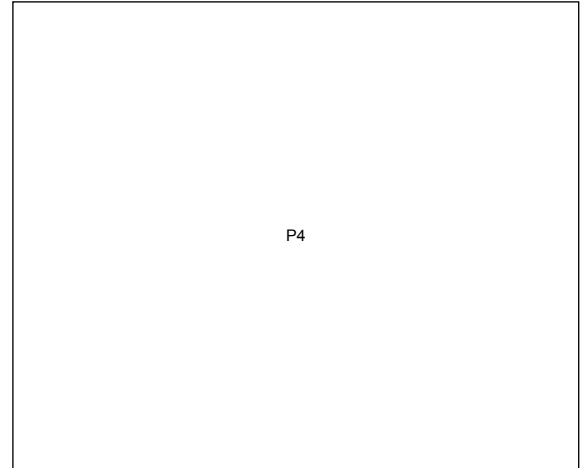
Note *1: L=2.77mH, V_{CC}=50V

Note *2: T_{ch}≦150°C

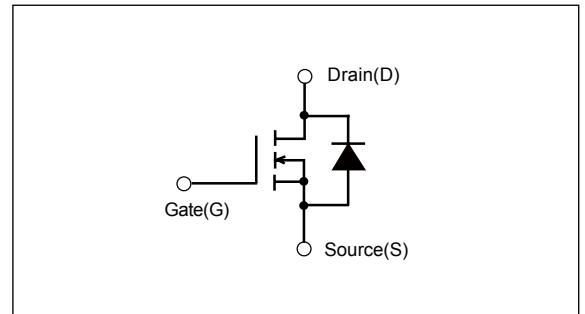
Note *3: I_F≦-I_D, -di/dt=50A/μs, V_{CC}≦BV_{DSS}, T_{ch}≦150°C

Note *4: V_{DS}≦500V

Outline Drawings



Equivalent circuit schematic



Electrical characteristics (T_c =25°C unless otherwise specified)

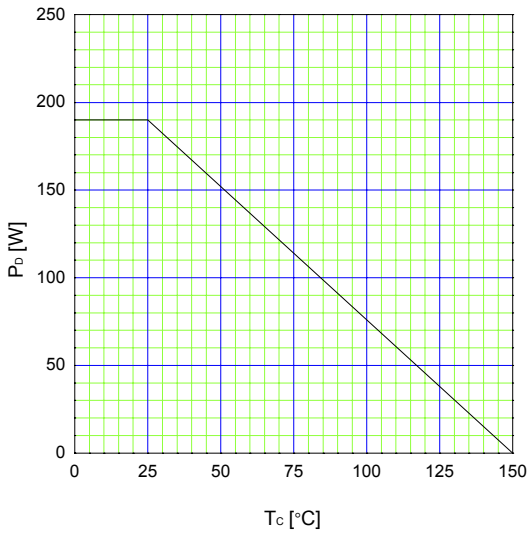
Items	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =250μA V _{GS} =0V	500			V
Gate threshold voltage	V _{GS(th)}	I _D = 250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =500V V _{GS} =0V T _{ch} =25°C			25	μA
		V _{DS} =400V V _{GS} =0V T _{ch} =125°C			250	
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{D(on)}	I _D =6A V _{GS} =10V		0.40	0.52	Ω
Forward transconductance	g _{fs}	I _D =6A V _{DS} =25V	5.5	11		S
Input capacitance	C _{iss}	V _{DS} =25V		1200	1800	pF
Output capacitance	C _{oss}	V _{GS} =0V		140	210	
Reverse transfer capacitance	C _{rss}	f=1MHz		6.0	9.0	
Turn-on time t _{on}	t _{d(on)}	V _{CC} =300V I _D =6A V _{GS} =10V		17	26	ns
			t _r		15	
Turn-off time t _{off}	t _{d(off)}	R _{GS} =10 Ω		34	51	
			t _f		7	
Total Gate Charge	Q _G	V _{CC} =250V		30	45	nC
Gate-Source Charge	Q _{GS}	I _D =12A		11	16.5	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		10	15	
Avalanche capability	I _{AV}	L=1.76mH T _{ch} =25°C	14			A
Diode forward on-voltage	V _{SD}	I _F =12A V _{GS} =0V T _{ch} =25°C		1.00	1.50	V
Reverse recovery time	t _{rr}	I _F =12A V _{GS} =0V		0.7		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		4.5		μC

Thermal Characteristics

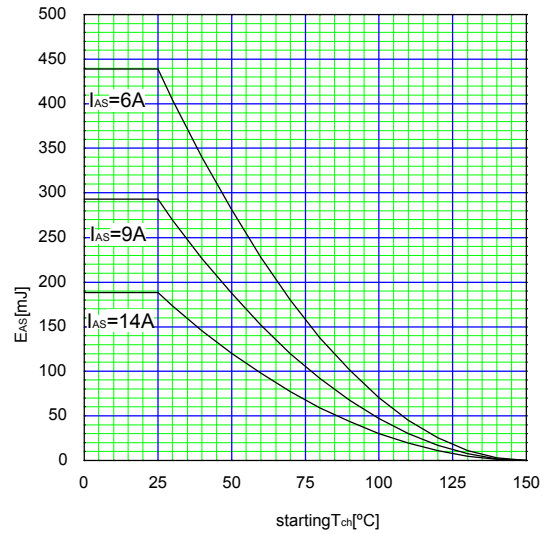
Items	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			0.641	°C/W
	R _{th(ch-a)}	channel to ambient			75.0	°C/W

■ Characteristics

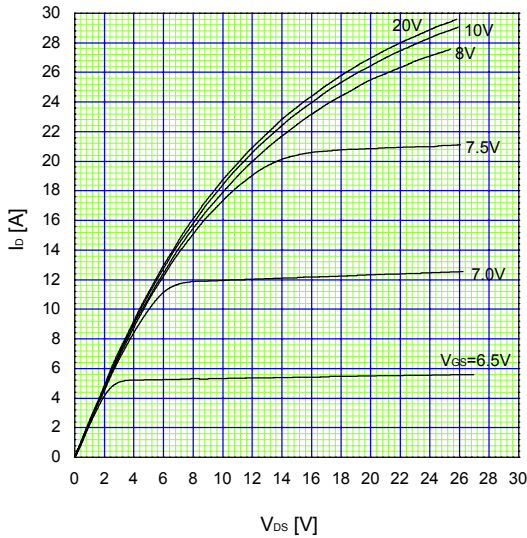
Allowable Power Dissipation
 $P_D=f(T_C)$



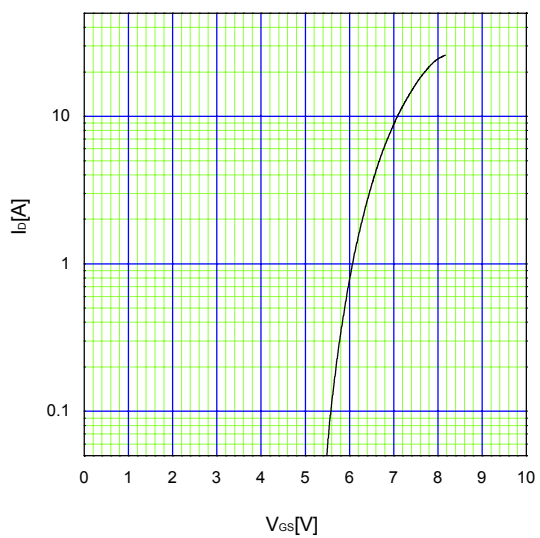
Maximum Avalanche Energy vs. starting T_{ch}
 $E_{AS}=f(\text{starting } T_{ch}): V_{CC}=50V$



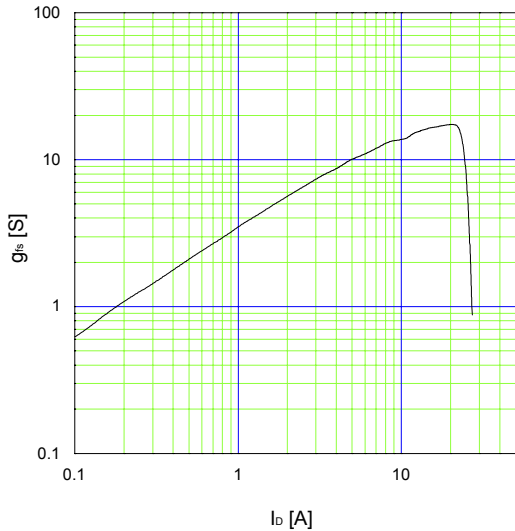
Typical Output Characteristics
 $I_D=f(V_{DS}): 80\mu s$ Pulse test, $T_{ch}=25^\circ C$



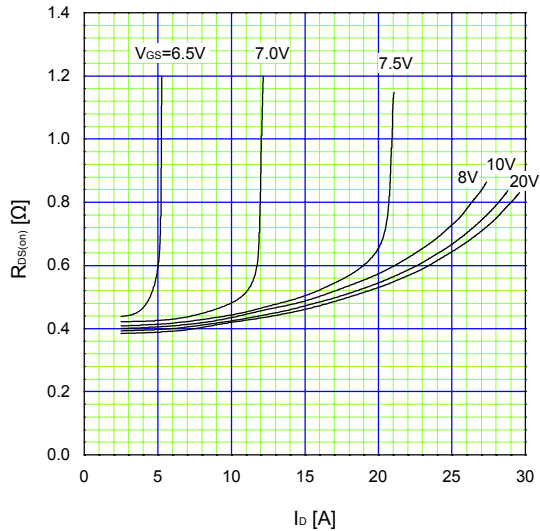
Typical Transfer Characteristic
 $I_D=f(V_{GS}): 80\mu s$ Pulse test, $V_{DS}=25V, T_{ch}=25^\circ C$



Typical Transconductance
 $g_{fs}=f(I_D): 80\mu s$ Pulse test, $V_{DS}=25V, T_{ch}=25^\circ C$

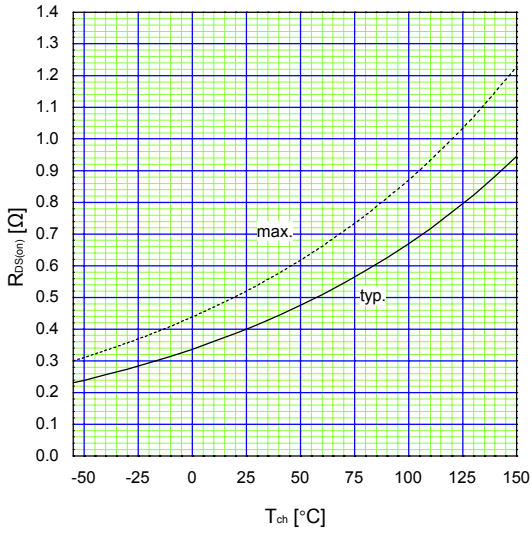


Typical Drain-Source on-state Resistance
 $R_{DS(on)}=f(I_D): 80\mu s$ Pulse test, $T_{ch}=25^\circ C$



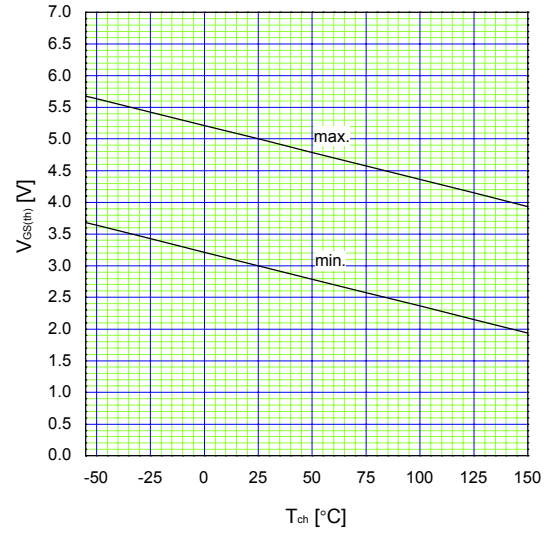
Drain-Source On-state Resistance

$R_{DS(on)}=f(T_{ch}):I_D=6A, V_{GS}=10V$



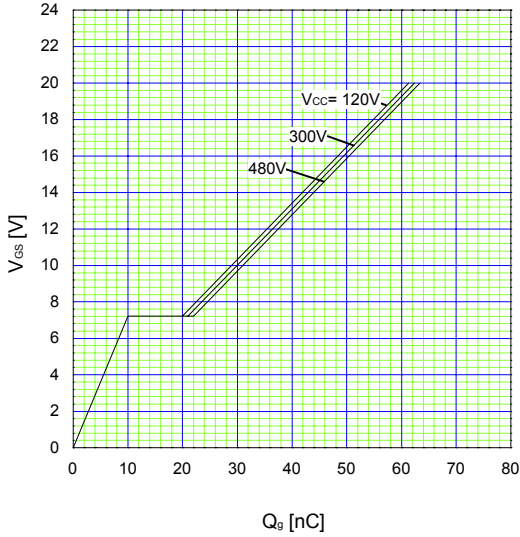
Gate Threshold Voltage vs. T_{ch}

$V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



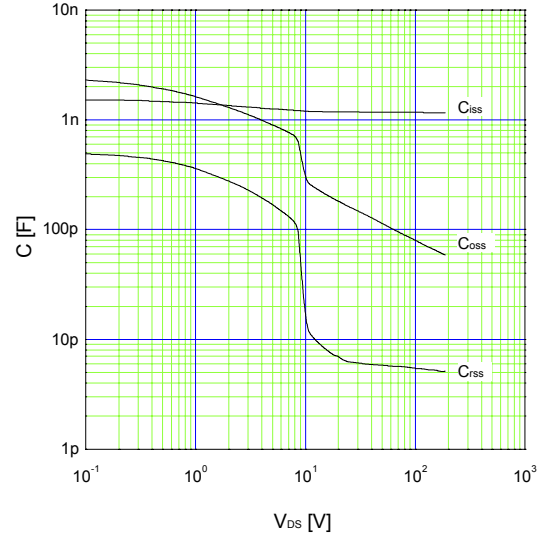
Typical Gate Charge Characteristics

$V_{GS}=f(Q_g):I_D=12A, T_{ch}=25^\circ C$



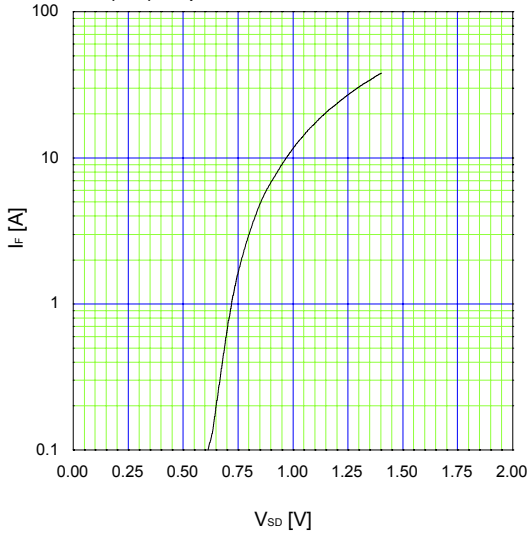
Typical Capacitance

$C=f(V_{DS}):V_{GS}=0V, f=1MHz$



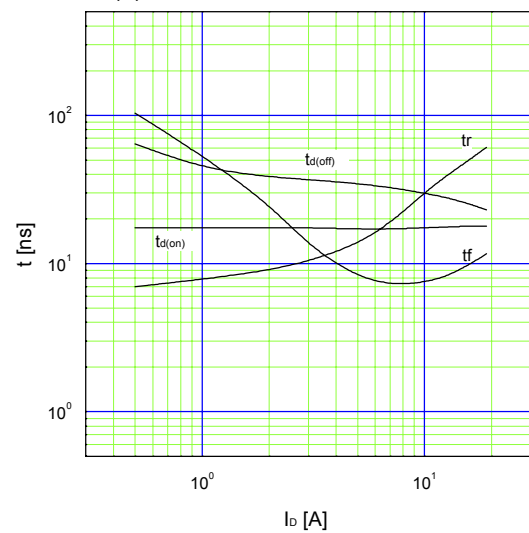
Typical Forward Characteristics of Reverse Diode

$I_F=f(V_{SD}):80\mu s \text{ Pulse test}, T_{ch}=25^\circ C$



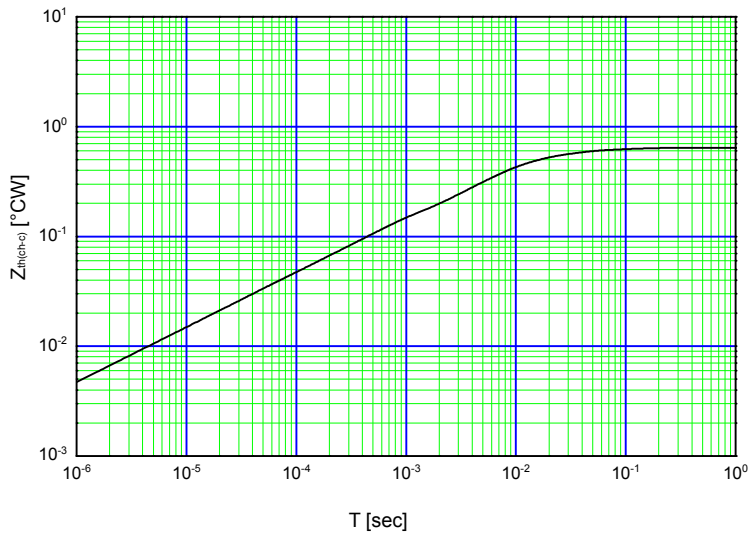
Typical Switching Characteristics vs. I_D

$t=f(I_D):V_{CC}=300V, V_{GS}=10V, R_G=10\Omega$



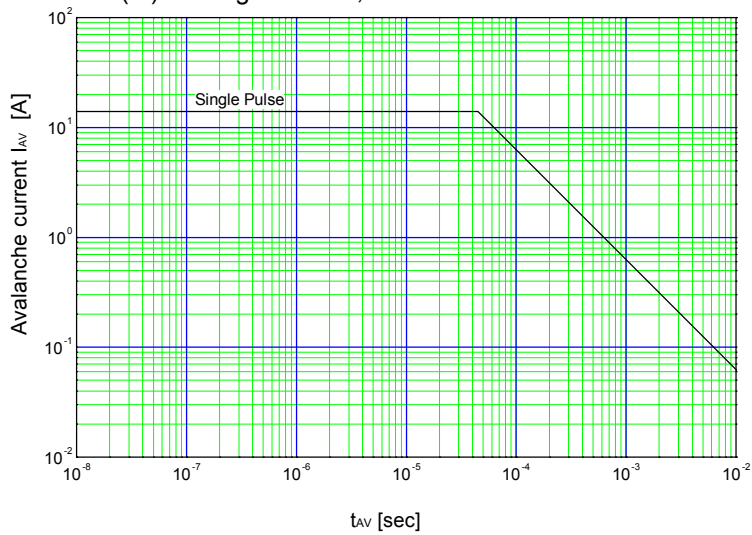
Maximum Transient Thermal Impedance

$Z_{th(ch-c)}=f(t); D=0$



Maximum Avalanche Current vs Pulse width

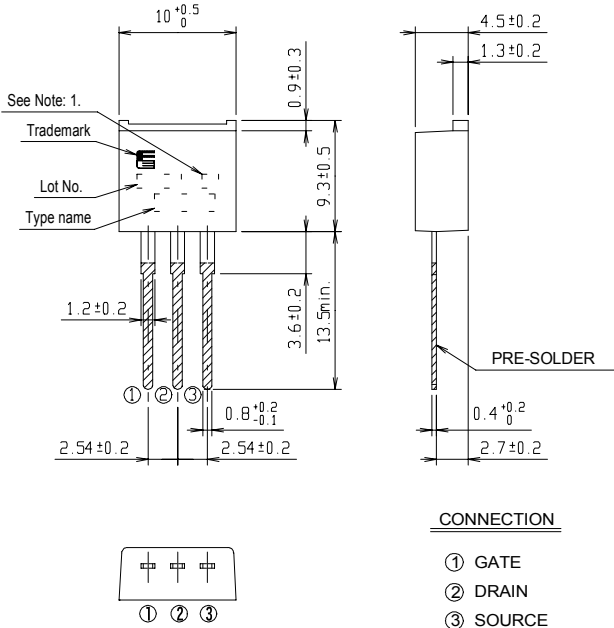
$I_{AV}=f(t_{AV}); \text{starting } T_{ch}=25^{\circ}C, V_{CC}=50V$



Outline Drawings [mm]

Type(L)

FUJI POWER MOS FET

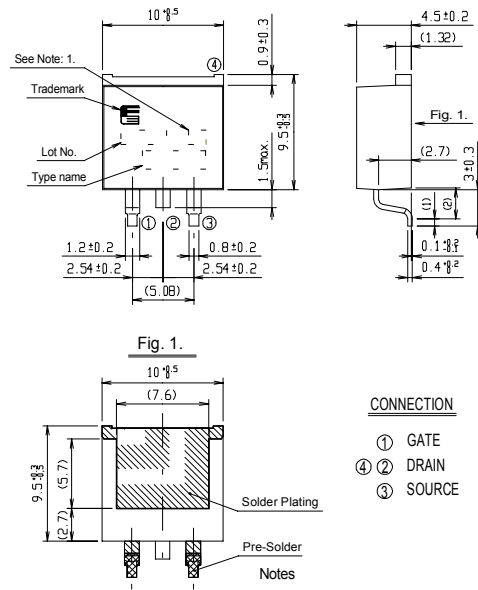


Note: 1. Guaranteed mark of avalanche ruggedness.

DIMENSIONS ARE IN MILLIMETERS.

Type(S)

FUJI POWER MOS FET

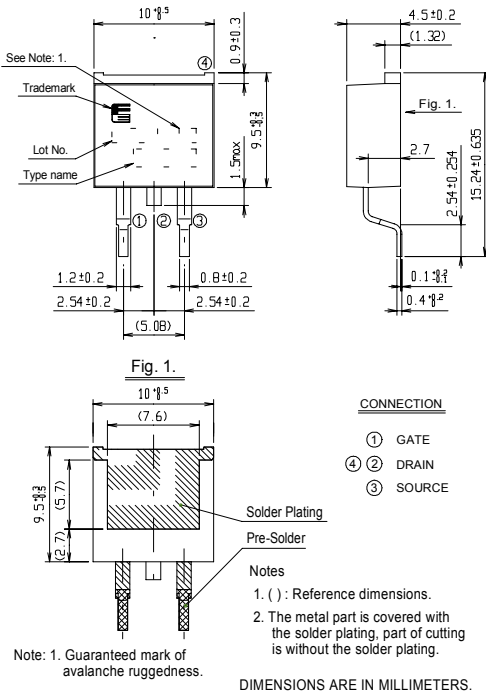


Note: 1. Guaranteed mark of avalanche ruggedness.

DIMENSIONS ARE IN MILLIMETERS.

Type(SJ)

FUJI POWER MOS FET



Note: 1. Guaranteed mark of avalanche ruggedness.

DIMENSIONS ARE IN MILLIMETERS.

WARNING

1. This Catalog contains the product specifications, characteristics, data, materials, and structures as of May 2012.
The contents are subject to change without notice for specification changes or other reasons. When using a product listed in this Catalog, be sure to obtain the latest specifications.
2. All applications described in this Catalog exemplify the use of Fuji's products for your reference only. No right or license, either express or implied, under any patent, copyright, trade secret or other intellectual property right owned by Fuji Electric Co., Ltd. is (or shall be deemed) granted. Fuji Electric Co., Ltd. makes no representation or warranty, whether express or implied, relating to the infringement or alleged infringement of other's intellectual property rights which may arise from the use of the applications described herein.
3. Although Fuji Electric Co., Ltd. is enhancing product quality and reliability, a small percentage of semiconductor products may become faulty. When using Fuji Electric semiconductor products in your equipment, you are requested to take adequate safety measures to prevent the equipment from causing a physical injury, fire, or other problem if any of the products become faulty. It is recommended to make your design failsafe, flame retardant, and free of malfunction.
4. The products introduced in this Catalog are intended for use in the following electronic and electrical equipment which has normal reliability requirements.
 - Computers
 - OA equipment
 - Communications equipment (terminal devices)
 - Measurement equipment
 - Machine tools
 - Audiovisual equipment
 - Electrical home appliances
 - Personal equipment
 - Industrial robots etc.
5. If you need to use a product in this Catalog for equipment requiring higher reliability than normal, such as for the equipment listed below, it is imperative to contact Fuji Electric Co., Ltd. to obtain prior approval. When using these products for such equipment, take adequate measures such as a backup system to prevent the equipment from malfunctioning even if a Fuji's product incorporated in the equipment becomes faulty.
 - Transportation equipment (mounted on cars and ships)
 - Trunk communications equipment
 - Traffic-signal control equipment
 - Gas leakage detectors with an auto-shut-off feature
 - Emergency equipment for responding to disasters and anti-burglary devices
 - Safety devices
 - Medical equipment
6. Do not use products in this Catalog for the equipment requiring strict reliability such as the following and equivalents to strategic equipment (without limitation).
 - Space equipment
 - Aeronautic equipment
 - Nuclear control equipment
 - Submarine repeater equipment
7. Copyright ©1996-2012 by Fuji Electric Co., Ltd. All rights reserved.
No part of this Catalog may be reproduced in any form or by any means without the express permission of Fuji Electric Co., Ltd.
8. If you have any question about any portion in this Catalog, ask Fuji Electric Co., Ltd. or its sales agents before using the product.
Neither Fuji Electric Co., Ltd. nor its agents shall be liable for any injury caused by any use of the products not in accordance with instructions set forth herein.